

EFC2K101NUZ

Power MOSFET for 1-Cell Lithium-ion Battery Protection

12 V, 6.2 mΩ, 15 A, Dual N-Channel

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-cell lithium-ion battery applications.

Features

- 2.5 V Drive
- Common-Drain Type
- ESD Diode-Protected Gate
- This device is Pb-Free, Halogen Free and RoHS Compliance

Applications

- 1-Cell Lithium-ion Battery Charging and Discharging Switch

Specifications

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	12	V
Gate to Source Voltage	V _{GSS}	±8	V
Source Current (DC)	I _S	15	A
Source Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I _{SP}	60	A
Total Dissipation (Note 1)	P _T	1.4	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	R _{θJA}	89.3	°C/W

1. Surface mounted on ceramic substrate (5000 mm² × 0.8 mm).

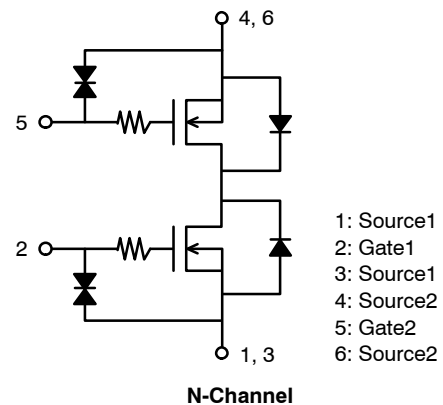


ON Semiconductor®

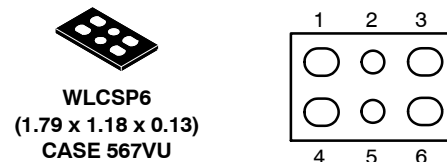
www.onsemi.com

V _{SSS}	R _{SS(ON)} MAX	I _S MAX
12 V	6.2 mΩ @ 4.5 V	15 A
	6.6 mΩ @ 3.8 V	
	8.0 mΩ @ 3.1 V	
	10.0 mΩ @ 2.5 V	

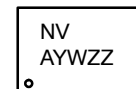
ELECTRICAL CONNECTION



PIN ASSIGNMENT



MARKING DIAGRAM



NV = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

EFC2K101NUZ

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)SSS}$	Source to Source Breakdown Voltage	$I_S = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	12			V
I_{SSS}	Zero-Gate Voltage Source Current	$V_{SS} = 10 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$			± 1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{SS} = 6 \text{ V}, I_S = 1 \text{ mA}$	0.4		1.3	V
$R_{SS(on)}$	Static Source to Source On-State Resistance	$I_S = 5 \text{ A}, V_{GS} = 4.5 \text{ V}$	3.2	4.7	6.2	$\text{m}\Omega$
		$I_S = 5 \text{ A}, V_{GS} = 3.8 \text{ V}$	3.5	5.0	6.6	$\text{m}\Omega$
		$I_S = 5 \text{ A}, V_{GS} = 3.1 \text{ V}$	3.9	5.7	8.0	$\text{m}\Omega$
		$I_S = 5 \text{ A}, V_{GS} = 2.5 \text{ V}$	4.5	6.6	10.0	$\text{m}\Omega$
$t_d(on)$	Turn-ON Delay Time	$V_{SS} = 5 \text{ V}, V_{GS} = 3.8 \text{ V}, I_S = 5 \text{ A}$ $R_g = 10 \text{ k}\Omega$ Switching Test Circuit		5		μs
t_r	Rise Time			19		μs
$t_d(off)$	Turn-OFF Delay Time			53		μs
t_f	Fall Time			40		μs
Qg	Total Gate Charge	$V_{SS} = 5 \text{ V}, V_{GS} = 3.8 \text{ V}, I_S = 5 \text{ A}$		16		nC
$V_{F(S-S)}$	Forward Source to Source Voltage	$I_S = 3 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

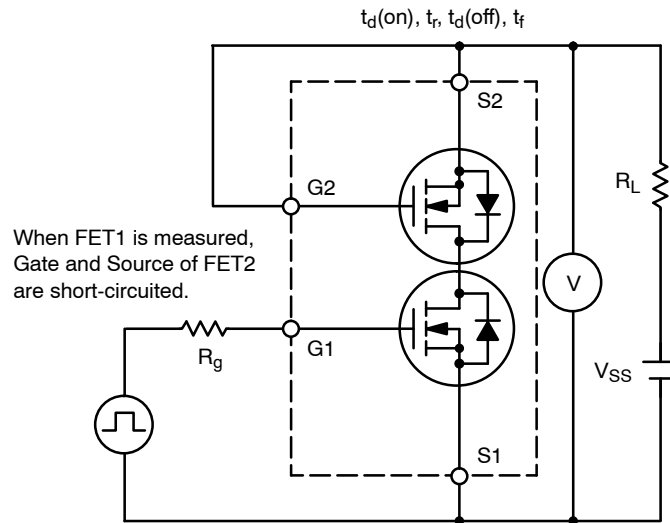


Figure 1. Switching Test Circuit

ORDERING INFORMATION

Device	Marking	Package	Shipping [†] (Qty / Packing)
EFC2K101NUZTDG	NV	WLCSP6, 1.79 x 1.18 x 0.13 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

TYPICAL CHARACTERISTICS

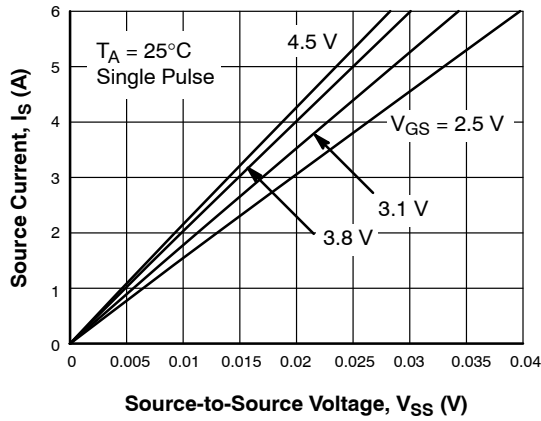


Figure 2. On-Region Characteristics

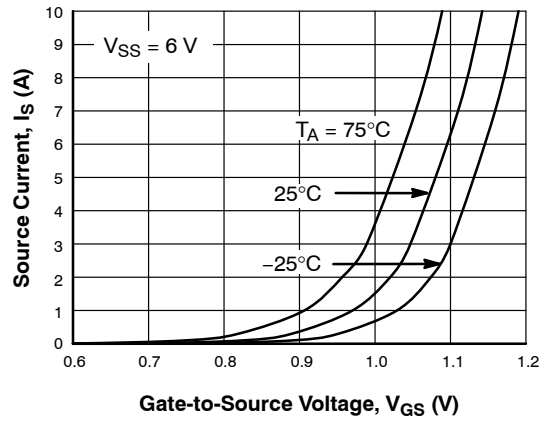


Figure 3. Transfer Characteristics

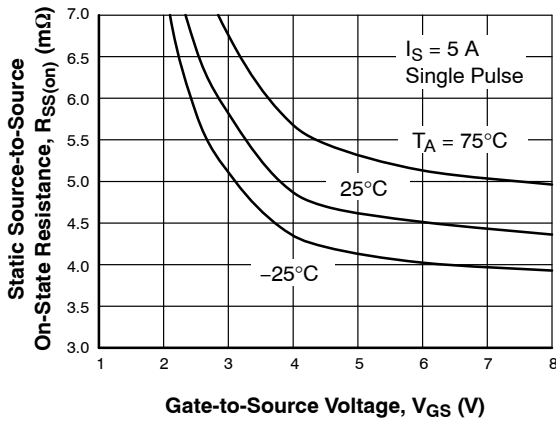


Figure 4. On-Resistance vs. Gate-to-Source Voltage

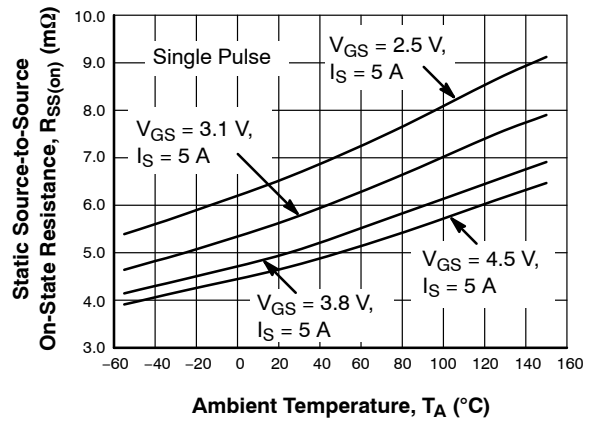


Figure 5. On-Resistance vs. Temperature

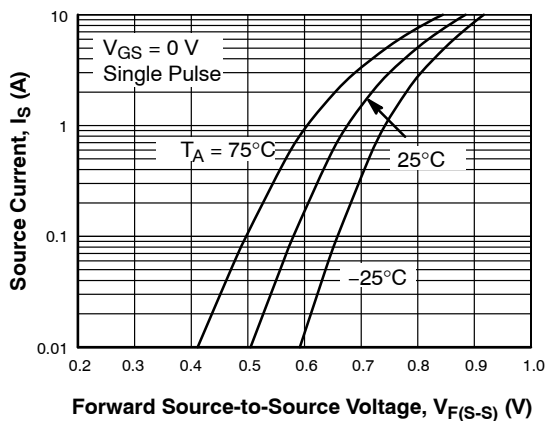


Figure 6. Forward Source-to-Source Voltage vs. Current

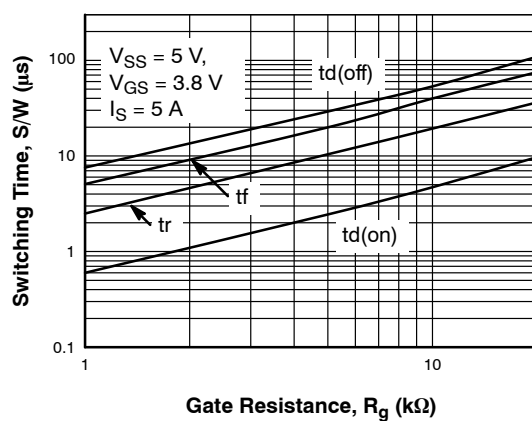


Figure 7. Switching Time vs. Gate Resistance

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TYPICAL CHARACTERISTICS

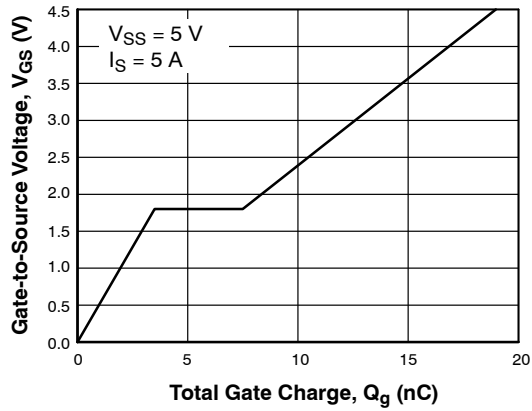


Figure 8. Gate-to-Source Voltage vs. Total Charge

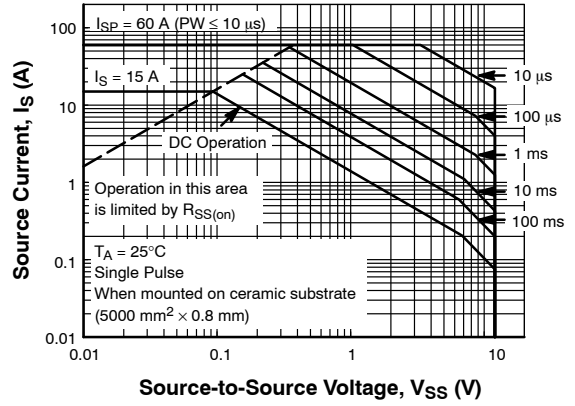


Figure 9. Safe Operating Area

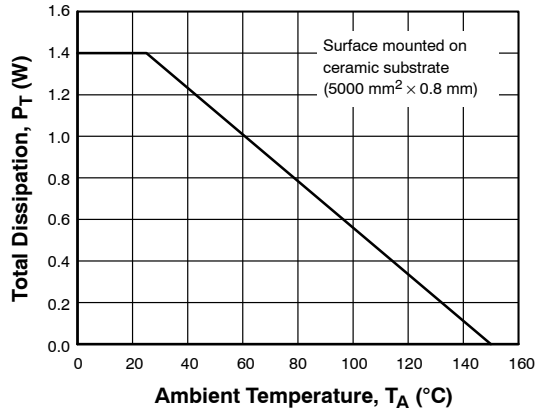


Figure 10. Total Dissipation vs. Temperature

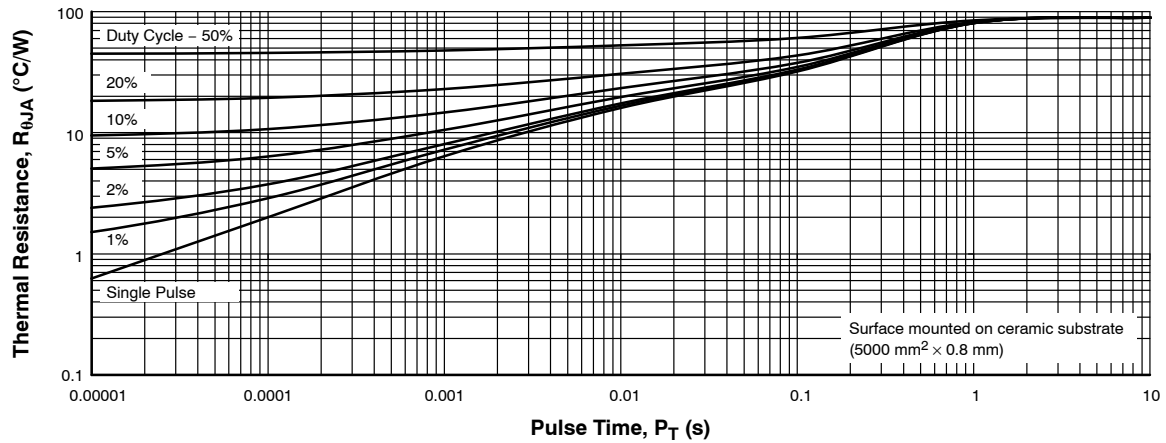
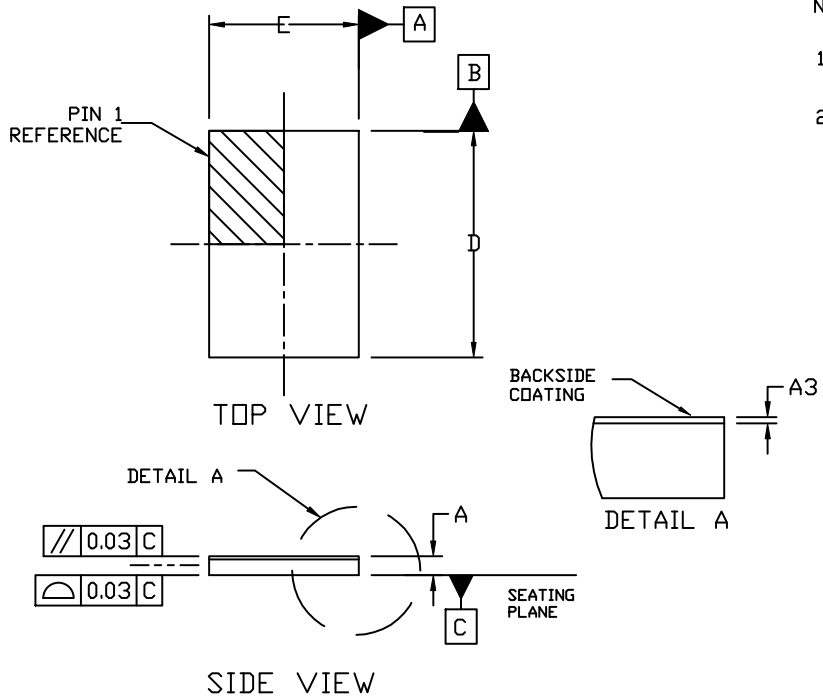


Figure 11. Thermal Response

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PACKAGE DIMENSIONS

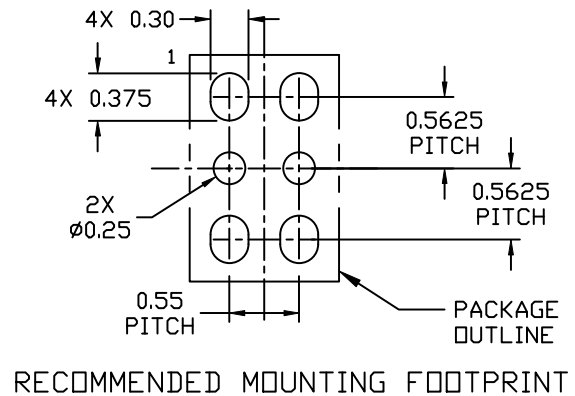
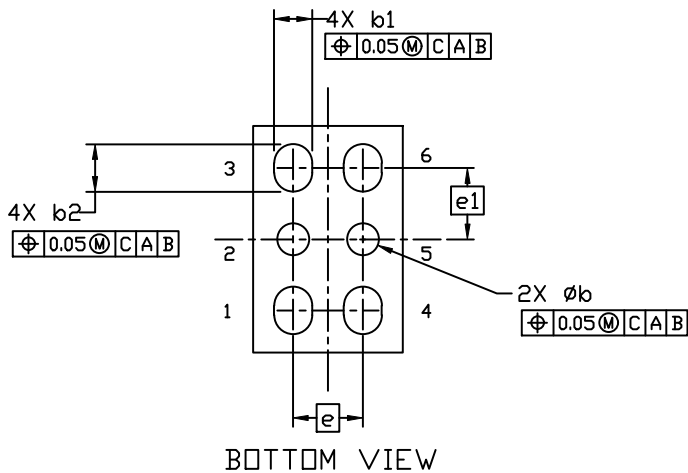
WLCSP6 1.79x1.18x0.13
CASE 567VU
ISSUE 0



NOTES:


1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.10	0.125	0.15
A3	0.025 REF		
b	0.22	0.25	0.28
b1	0.27	0.30	0.33
b2	0.345	0.375	0.405
D	1.76	1.79	1.82
E	1.15	1.18	1.21
e	0.55 BSC		
e1	0.5625 BSC		



EFC2K101NUZ

Note on Usage: Since the EFC2K101NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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